

Sheet 1 of 1

Form 1449*	Atty. Docket No. 3042US1	Serial No. 09/382,442
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Alan R. Reinberg	
	Filing Date: August 25, 1999	Group: 2818

U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
RRB	5,045,488	09/03/1991	Yeh, B.	437	43	01/22/90
RRB	5,098,866	03/24/1992	Clark, D.R., et al.	437	239	12/27/88
RRB	5,132,237	07/21/1992	Matthews, J.A.	437	40	01/28/91
RRB	5,229,311	07/20/1993	Lai, S.K., et al.	437	43	03/25/92
RRB	5,706,552	01/13/1998	Hsieh, T.W.	16	82	08/30/96
RRB	5,818,710	10/06/1998	LeVan Suu, M.	364	141	06/02/97

FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
RRB						

OTHER DOCUMENTS

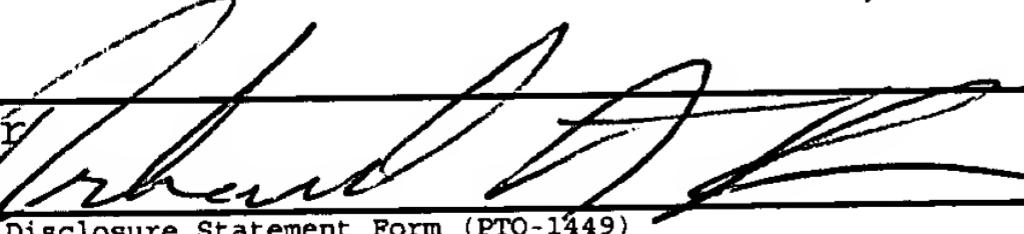
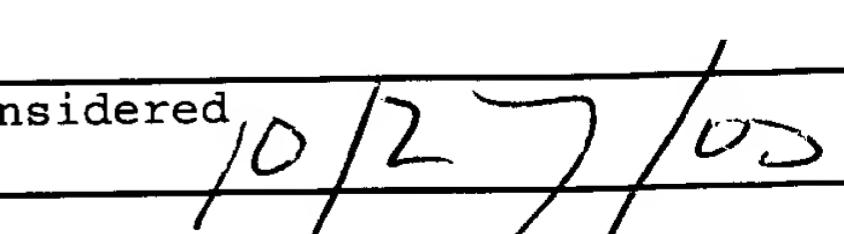
(Including Author, Title, Date, Pertinent Pages, Etc.)

RRB	"TN-28-01 Boot Block Flash Memory", <u>Micron Quantum Devices, Inc.</u> , pp. 5-9 - 5-11, (1997)
RRB	Fong, Y., et al., "Oxides Grown on Textured Single-Crystal Silicon-- Dependence on Process and Application in EEPROMs", <u>IEEE Transactions on Electron Devices</u> , 37(3), pp. 583-590, (March 1990)
RRB	Hess, K., et al., "Giant Isotope Effect in Hot Electron Degradation of Metal Oxide Silicon Devices", <u>IEEE Transactions on Electron Devices</u> , 45(2), pp. 406-416, (February 1998)
RRB	Hsu, F.C., et al., "Effect of Final Annealing on Hot-Electron-Induced MOSFET Degradation", <u>IEEE Electron Device Letters</u> , EDL-6(7), pp. 369-371, (July 1985)
RRB	Rees, Jr., W.S., <u>CVD of Nonmetals</u> , ISBN 3-527-29295-0, Table of Contents, (1996)

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*Substitute Disclosure Statement Form (PTO-1449)

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